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## **Inclosure Material:** Metal **Overall Length:** Between 0.240 inches and 0.260 inches **Terminal Length:** Between 0.500 inches and 0.750 inches **Overall Diameter:** Between 0.335 inches and 0.370 inches **Function For Which Designed:** Reverse blocking **Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-5 Electrode Internally-electrically Connected To Case: Anode **Mounting Method:** Terminal **Features Provided:** Quality assurance level tx **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 2.2 forward voltage, peak and 1.0 gate trigger voltage, dc **Current Rating Per Characteristic:** 2.00 milliamperes forward current, total rms peak and 0.22 amperes forward current, total rms megahertz Maximum Operating Tempurature Per Measurement Point: 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 3 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/276 government specification Shelf Life: N/a Unit Of Measure: **Demilitarization:** No

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